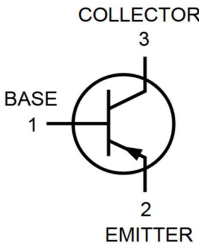
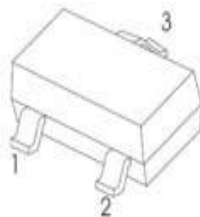


TRANSI STOR (PNP)	SOT-23 Plastic-Encapsulate Transistors		
<u>SOT-23</u>  1.BASE 2.EMITTER 3.COLLECTOR Marking :Y2			
	Features ※ Complimentary to SS8050 ※ Collector Current: Ic=1.5A		
MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)			
Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	-40	V
Collector-Emitter Voltage	VCEO	-25	V
Emitter-Base Voltage	VEBO	-5	V
Collector Current	IC	-1500	mA
Collector Power Dissipation	PC	300	mW
Thermal Resistance From Junction To Ambient	RθJA	417	℃/W
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55~+150	℃

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V (BR) CBO	IC= 100 μ A, IE=0	-40			V
Collector-emitter breakdown voltage	V (BR) CEO	IC= 1mA, IB=0	-25			V
Emitter-base breakdown voltage	V (BR) EBO	IE=100 μ A, IC=0	-5			V
Collector cut-off current	ICBO	VCB=40 V , IE=0			-0.1	μ A
Collector cut-off current	ICEO	VCE=25V , IB=0			-0.1	μ A
Emitter cut-off current	IEBO	VEB= 5V , IC=0			-0.1	μ A
DC current gain	hFE	VCE=1V, IC= 50mA	120		400	
	hFE	VCE=1V, IC= 500mA	40			
Collector-emitter saturation voltage	VCE(sat)	IC=500 mA, IB= 50mA			-0.5	V
Base-emitter saturation voltage	VBE(sat)	IC=500 mA, IB= 50mA			-1.2	V
Transition frequency	fT	VCE=6V, IC= 20mA f=30MHz	150			MHz

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

